



INTEGRATED RELAY AND INDUCTIVE LOAD DRIVER

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C	
60V	1.8Ω @ V _{GS} = 5V	620m A	
600	2.4Ω @ V _{GS} = 3V	- 630mA	

Description and Applications

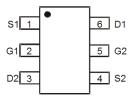
DIODES™ DMN61D8LVTQ provides a single component solution for switching inductive loads such as relays, solenoids, and small DC motors in automotive applications, without the need of a freewheeling diode. DMN61D8LVTQ accepts logic level inputs, thus allowing it to be driven by logic gates, inverters and microcontrollers. It is ideally suited for door, window and antenna relay coils.











Top View

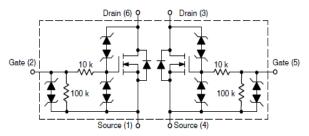
Features and Benefits

- Provides a reliable and robust interface between sensitive logic and DC relay coils
- Replaces 3 to 4 discrete components enabling PCB footprint to be reduced
- Internal active clamp removes the need for external zener diode
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN61D8LVTQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: TSOT26
- Package Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 63
- Weight: 0.013 grams (Approximate)



Equivalent Circuit

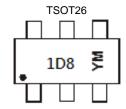
Ordering Information (Note 4)

Part Number	Package	Packing		
Fait Number	Fackage	Qty.	Carrier	
DMN61D8LVTQ-7	TSOT26	3,000	Tape & Reel	
DMN61D8LVTQ-13	TSOT26	10,000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



1D8 = Product Type Marking Code YM = Date Code Marking Y or Y= Year (ex: J = 2022) M = Month (ex: 9 = September)

Date Code Key

Date Code Ney												
Year	2015		2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	С		J	K	L	M	N	0	Р	R	S	Т
	1	1	1	1							1	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	60	V	
Gate-Source Voltage	V _{GSS}	±12	V		
Continuous Drain Current (Note 6)	Steady State	T _A = +25°C T _A = +70°C	lo	630 500	mA
Maximum Continuous Body Diode Forward Current	Maximum Continuous Body Diode Forward Current (Note 6)				Α
Single Pulse Drain-to-Source Avalanche Energy (For Relay's Coils/Inductive Loads of 80Ω or Higher) (T _J Initial = +85°C)			EZ	200	mJ
Peak Power Dissipation, Drain-to-Source (Non repopulse 1.0ms duration) (T _J Initial = +85°C)	k Power Dissipation, Drain-to-Source (Non repetitive current square e 1.0ms duration) (T _J Initial = +85°C)		PPK	20	W
	tump Pulse, Drain-to-Source, R _{SOURCE} = 0.5Ω , t = 300ms) elay's Coils/Inductive Loads of 80Ω or Higher) (T _J Initial = $+85^{\circ}$ C)		ELD1	60	V
Inductive Switching Transient 1, Drain-to-Source (Waveform: R _{SOURCE} = 10Ω , t = $2.0ms$) (For Relay's Coils/Inductive Loads of 80Ω or Highe	ıl = +85°C)	ELD2	100	٧	
Inductive Switching Transient 2, Drain-to-Source (Waveform: R _{SOURCE} = 4.0Ω , t = 50μ s) (For Relay's Coils/Inductive Loads of 80Ω or Highe	r) (T」Initia	ELD3	300	V	
Reverse Battery, 10 Minutes (Drain-to-Source) (For Relay's Coils/Inductive Loads of 80Ω or more)	ı	Rev-Bat	-14	V	
Dual Voltage Jump Start, 10 Minutes (Drain-to-Sou	ırce)		Dual-Volt	28	V
ESD Human Body Model (HBM)			ESD	4,000	V

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P _D	820	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	154	°C/W	
Total Power Dissipation (Note 6)	PD	1,090	mW	
Thermal Resistance, Junction to Ambient (Note 6) Steady State		Reja	116	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Notes:

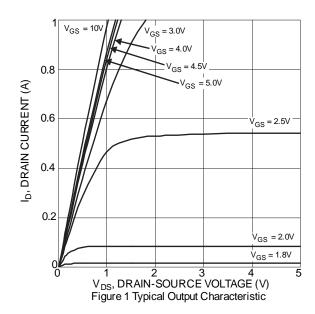
^{5.} Device mounted on FR-4 PCB, with minimum recommended pad layout.6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. copper, single sided.

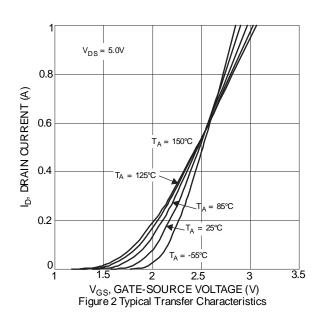


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	60			V	$V_{GS} = 0V$, $I_D = 10mA$	
Zero Gate Voltage Drain Current	IDSS			50 0.5	μA	V _{DS} = 60V, V _{GS} = 0V V _{DS} = 12V, V _{GS} = 0V	
Gate-Source Leakage	Igss		_	±90 ±60	μA	$V_{GS} = \pm 5V$, $V_{DS} = 0V$ $V_{GS} = \pm 3V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	1.3		2.0	V	V _{DS} = V _{GS} , I _D = 1mA	
Static Drain-Source On-Resistance	D		1.1	1.8	0	V _G S = 5V, I _D = 0.15A	
Static Drain-Source Off-Resistance	R _{DS(ON)}	_	1.4	2.4	12	V _G S = 3V, I _D = 0.15A	
Forward Transfer Admittance	Y _{fs}	80	_	_	ms	V _{DS} = 12V, I _D = 0.15A	
Diode Forward Voltage	VsD		0.8	1.2	V	V _G S = 0V, I _S = 0.15A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}		12.9		pF		
Output Capacitance	Coss		17	_	pF	V _{DS} = 12V, V _{GS} = 0V f = 1.0MHz	
Reverse Transfer Capacitance	Crss		0.84	_	pF	1 - 1.000112	
Total Gate Charge	Qg		0.74	_	nC		
Gate-Source Charge	Qgs		0.19	_	nC	$V_{GS} = 5V, V_{DS} = 12V,$ $I_{D} = 150 \text{mA}$	
Gate-Drain Charge	Qgd	_	0.16	_	nC	1D = 150MA	
Turn-On Delay Time	tD(ON)	_	131	_	ns		
Turn-On Rise Time	t _R	_	301	_	ns	\/ 40\/ \/ 5\/	
Turn-Off Delay Time	tD(OFF)		582		ns	$V_{DD} = 12V$, $V_{GS} = 5V$	
Turn-Off Fall Time	tF	_	440	_	ns		

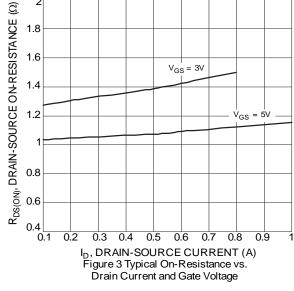
7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing. Notes:

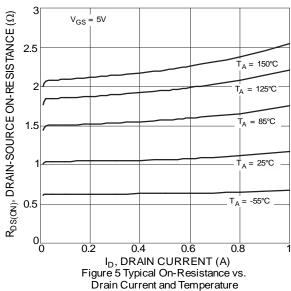


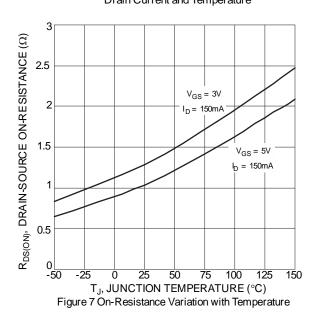


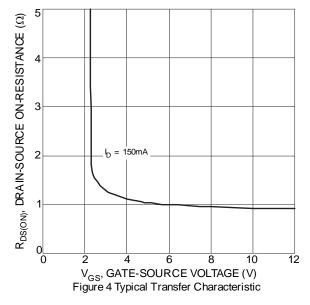


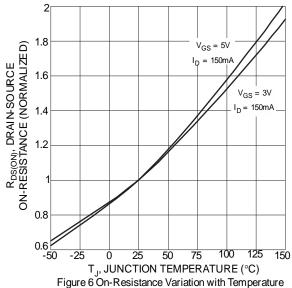












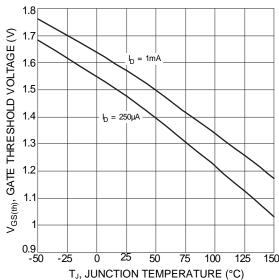
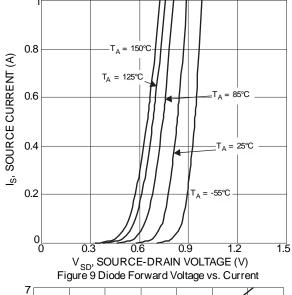
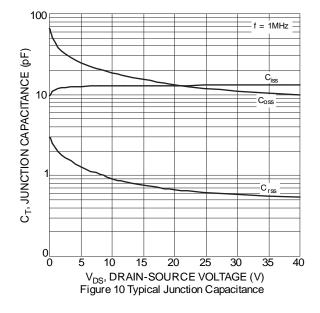


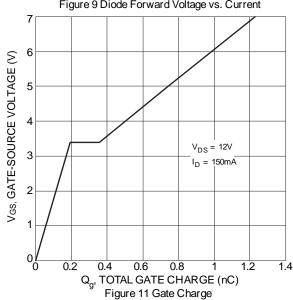
Figure 8 Gate Threshold Variation vs. Junction Temperature

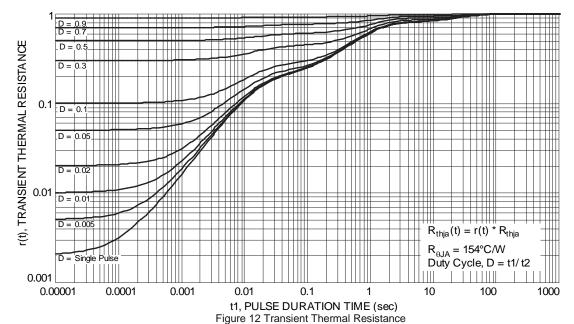










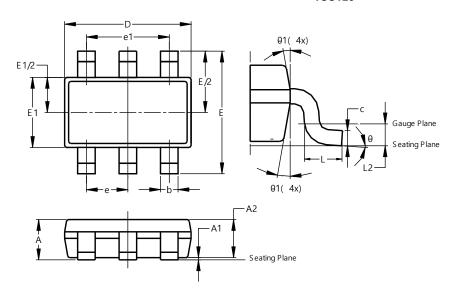




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26

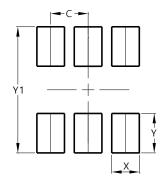


TSOT26								
Dim	Min	Max	Тур					
Α	-	1.00	-					
A1	0.010	0.100	-					
A2	0.840	0.900	-					
D	2.800	3.000	2.900					
Е	2	.800 BS	С					
E1	1.500	1.700	1.600					
b	0.300	0.450	1					
С	0.120	0.200	-					
е	0.950 BSC							
e1	1	1.900 BSC						
_	0.30	0.50	1					
L2	0.250 BSC							
θ	0°	8°	4°					
θ1	4°	12°	=					
Δ	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3 200



IMPORTANT NOTICE

- 1. DIODES INCORPORATED (Diodes) AND ITS SUBSIDIARIES MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).
- 2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes' products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes' products. Diodes' products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of Diodes' products for their intended applications, (c) ensuring their applications, which incorporate Diodes' products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.
- 3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.
- 4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.
- 5. Diodes' products are provided subject to Diodes' Standard Terms and Conditions of Sale (https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.
- 6. Diodes' products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes' products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.
- 7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.
- 8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.
- 9. This Notice may be periodically updated with the most recent version available at https://www.diodes.com/about/company/terms-and-conditions/important-notice

DIODES is a trademark of Diodes Incorporated in the United States and other countries. The Diodes logo is a registered trademark of Diodes Incorporated in the United States and other countries. © 2022 Diodes Incorporated. All Rights Reserved.

www.diodes.com